## **SPTECH Silicon NPN Power Transistor**

2SD998

#### **DESCRIPTION**

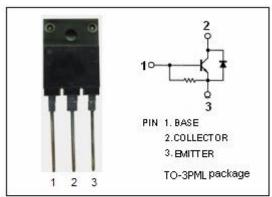
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 50V(Min)
- · Low Collector Saturation Voltage-
  - : V<sub>CE(sat)</sub>= 0.5V(Max)@ I<sub>C</sub>= 5A

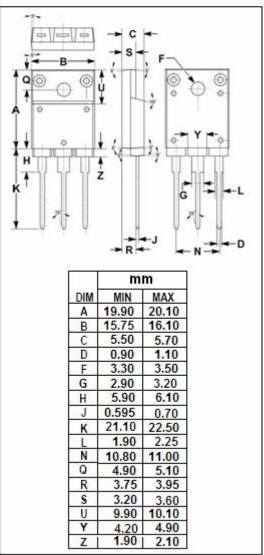
#### **APPLICATIONS**

 Designed for DC-DC converter, emergency lighting inverter and general purpose applications

### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	120	V	
V <sub>EBO</sub>	Emitter-Base Voltage	15	V	
Ic	Collector Current-Continuous	10	А	
Іср	Collector Current-Peak	25	А	
I <sub>B</sub>	Base Current-Continuous	4	А	
Pc	Collector Power Dissipation @ T <sub>c</sub> =25℃	80	W	
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	





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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 25mA; I <sub>B</sub> = 0	50			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 80mA			0.5	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 80mA			1.2	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V ; I <sub>E</sub> = 0			10	μА		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 15V ; I <sub>C</sub> = 0			10	μА		
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 1V	60		360			
f⊤	Current-Gain—Bandwidth Product	I <sub>E</sub> = -1A ; V <sub>CE</sub> = 12V		18		MHz		
Сов	Output Capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		210		pF		
Switching times								
t <sub>on</sub>	Turn-on Time			0.5		μs		
t <sub>stg</sub>	Storage Time	$I_{C}$ = 5A , $I_{B1}$ = 80mA; $I_{B2}$ = 80mA $R_{L}$ = 4 $\Omega$ ; $V_{CC}$ = 20V		2.0		μs		
t <sub>f</sub>	Fall Time			0.4		μs		

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